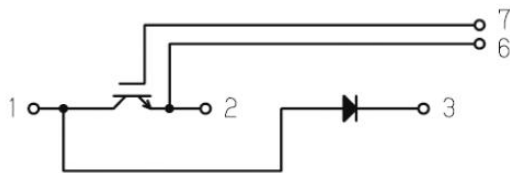
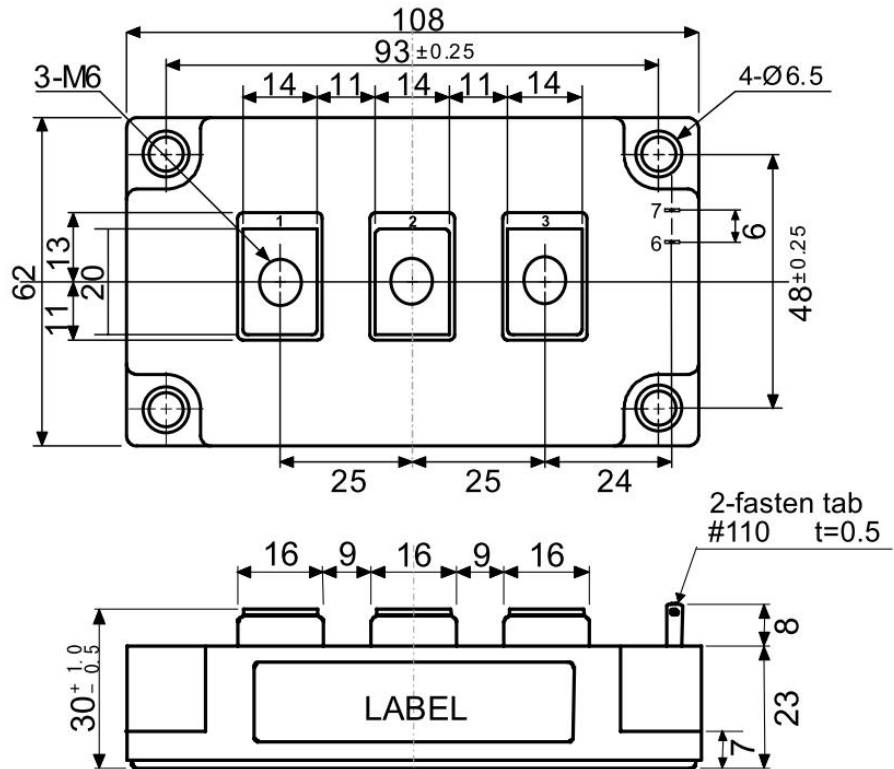


□ 回路図 : *CIRCUIT*

□ 概略図 : *SCHEMATIC DIAGRAM*

Dimension: [mm]


□ 最大定格 : *MAXIMUM RATINGS* (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

Item			Symbol	Condition	Rated Value	Unit
IGBT	コレクタ・エミッタ間 電 圧 Collector-Emitter Voltage		V _{CES}	G-E Short	1200	V
	ゲート・エミッタ間 電 圧 Gate-Emitter Voltage		V _{GES}	C-E Short	±20	V
	コ レ ク タ 電 流 Collector Current		I _C	DC T _C =85℃	300	A
			I _{CP}	Pulse ≤ 1ms	600	
	コ レ ク タ 損 失 Collector Power Dissipation		P _C	T _J =175℃	1578	W
T _J =150℃				1315		
Diode	繰 り 返 し ピ ー ク 逆 電 圧 Repetitive peak reverse voltage		V _{RRM}		1200	V
	順 電 流 Forward Current		I _F		300	A
			I _{FM}	Pulse ≤ 1ms	600	
最 大 接 合 温 度 Maximum Junction Temperature			T _{JMAX}	瞬時動作(過負荷) Instantaneous Overload	175	℃
接 合 温 度 Junction Temperature Range			T _J		−40~+150	℃
保 存 温 度 Storage Temperature Range			T _{stg}		−40~+125	℃
絶 縁 耐 圧 Isolation Voltage			V _{ISO}	Terminal to Base AC,1minute	2,500	V (RMS)
締 め 付 け ト ル ク Mounting Torque		Module Base to Heatsink	F _{tor}	M6	3	N・m
		Busbar to Main Terminal		M6	3	

□ 電 氣 的 特 性 : **ELECTRICAL CHARACTERISTICS** (at $T_J=25^\circ\text{C}$ unless otherwise specified)

Characteristic		Symbol	Test Condition		Min.	Typ.	Max.	Unit
IGBT	コレクタ遮断電流 Collector-Emitter Cut-Off Current	ICES	VCE= 1200V,VGE= 0V		—	—	1.0	mA
	ゲート漏れ電流 Gate-Emitter Leakage Current	IGES	VGE= ±20V,VCE= 0V		—	—	1.0	μA
	コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	VCE(sat.)	IC= 300A,VGE= 15V (chip level)	TJ=25°C	—	1.50	2.00	V
				TJ=125°C	—	1.70	—	
				TJ=150°C	—	1.80	—	
	ゲートしきい値電圧 Gate-Emitter Threshold Voltage	VGE(th.)	VCE= 10V,IC= 10mA		4.8	—	7.0	V
	入力容量 Input Capacitance	Cies	VCE= 25V,VGE= 0V,f= 1MHz		—	30.0	—	nF
	出力容量 Output Capacitance	Coes			—	0.86	—	
	帰還容量 Reverse Transfer Capacitance	Cres			—	0.70	—	
	ゲート電荷量 Gate Charge	Qg	VCC=600V, IC=300A, VGE=-15~+15V		—	3300	—	nC
スイッチング時間 Switching Time	上昇時間 Rise Time	tr	VCC= 600V Inductive Load IC= 300A RG= 2.4Ω VGE= ±15V TJ= 150°C		—	90	—	ns
	ターンオン遅延時間 Turn-on Delay Time	td(on)			—	220	—	
	下降時間 Fall Time	tf			—	290	—	
	ターンオフ遅延時間 Turn-off Delay Time	td(off)			—	800	—	
Diode	順電圧 Peak Forward Voltage	VF	IF= 300A,VGE=0V (chip level)	TJ=25°C	—	2.00	2.60	V
				TJ=125°C	—	1.98	—	
				TJ=150°C	—	1.95	—	
	逆回復時間 Reverse Recovery Time	trr	VCC= 600V Inductive Load IF= 300A RG= 2.4Ω VGE= ±15V TJ= 150°C		—	250	—	ns

□ 熱 的 特 性 : **THERMAL CHARACTERISTICS**

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱 抵 抗 Thermal Resistance	IGBT	$R_{th(j-c)}$	Junction to Case	—	—	0.095	$^\circ\text{C}/\text{W}$
	Diode		Per 1 Arm (Tc測定点:チップ直下)	—	—	0.15	

特性図 : CHARACTERISTICS CURVES

Fig.1- Output Characteristics (Typical)

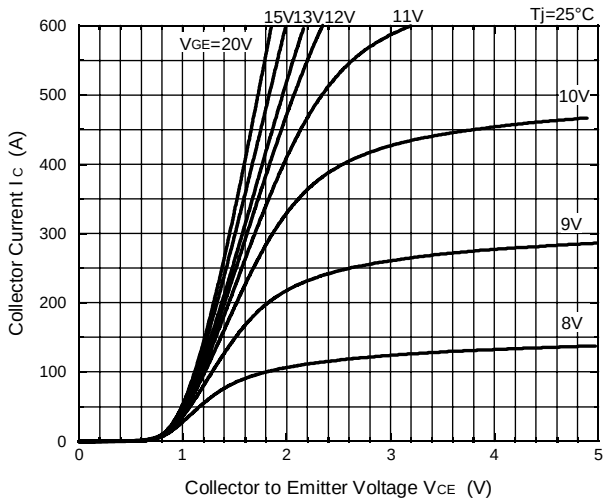


Fig.2- Saturation Voltage Characteristics (Typical)

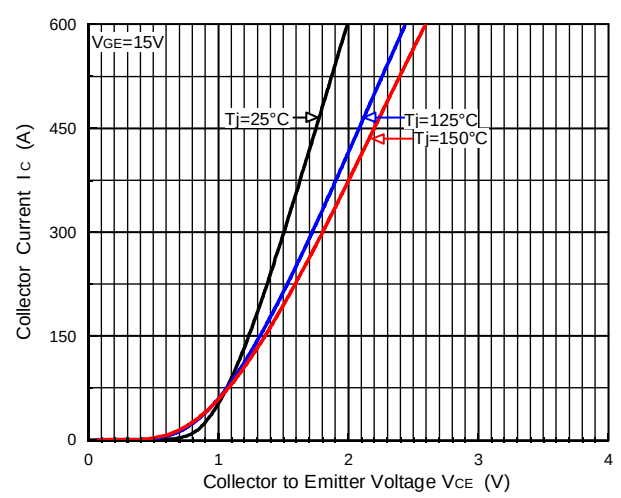


Fig.3- Transfer Characteristics (Typical)

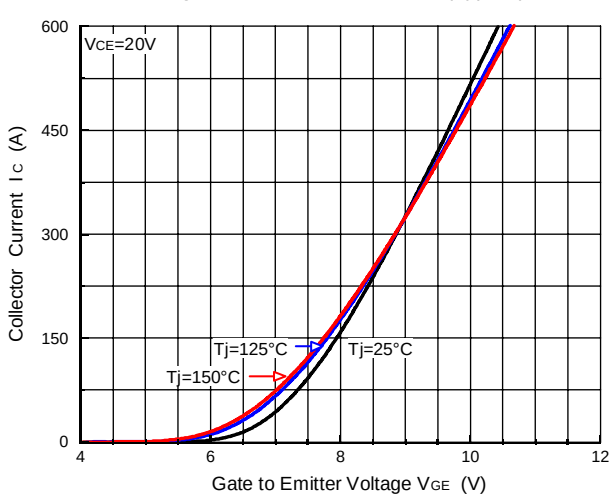


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

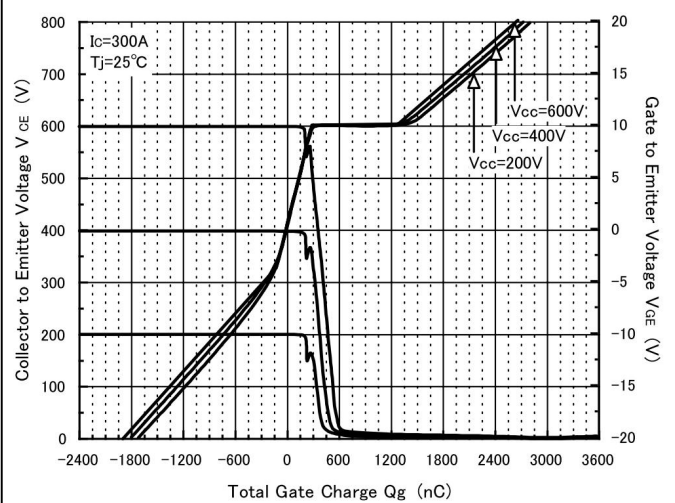


Fig.5- Collector Current vs. Switching Time

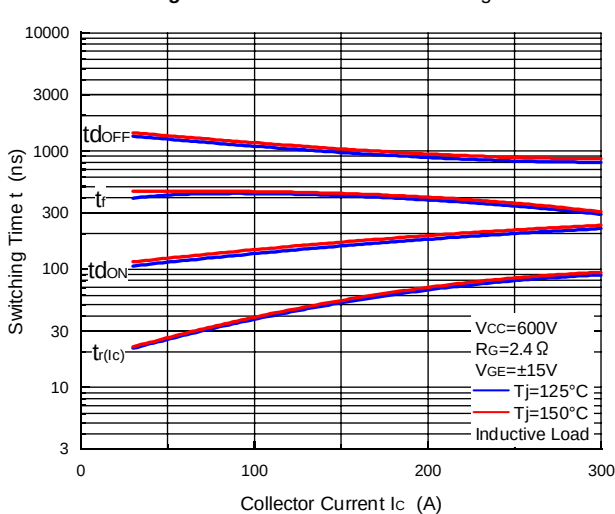
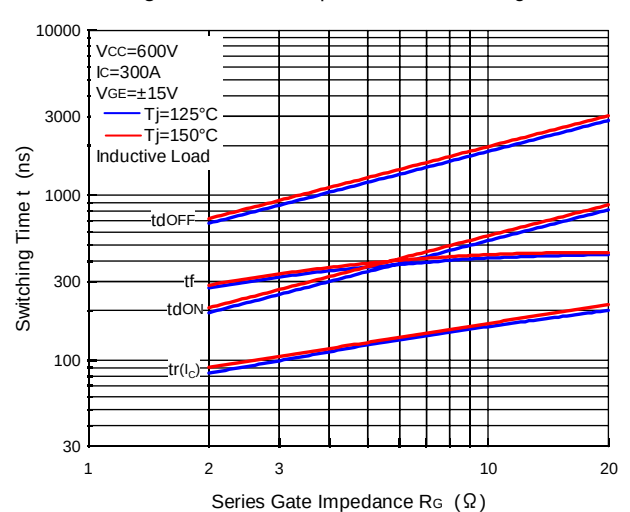


Fig.6- Series Gate Impedance vs. Switching Time



特性図 : CHARACTERISTICS CURVES

Fig.7- Collector Current vs. Switching Loss

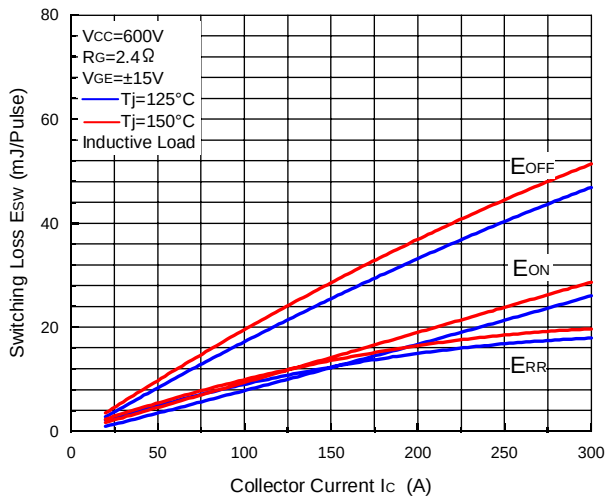


Fig.8- Series Gate Impedance vs. Switching Loss

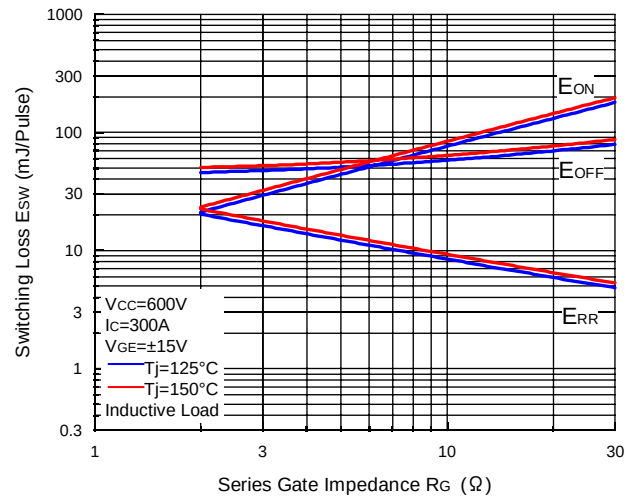


Fig.9- Forward Characteristics of FWD (Typical)

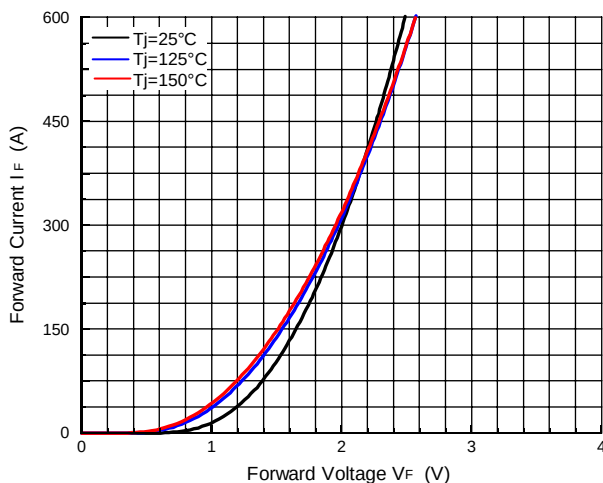


Fig.10- FWD Reverse Recovery Characteristics (Typical)

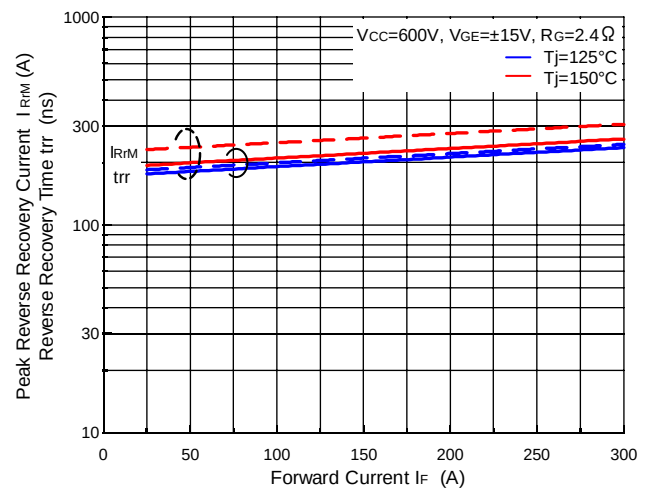


Fig.11- Reverse Bias Safe Operating Area

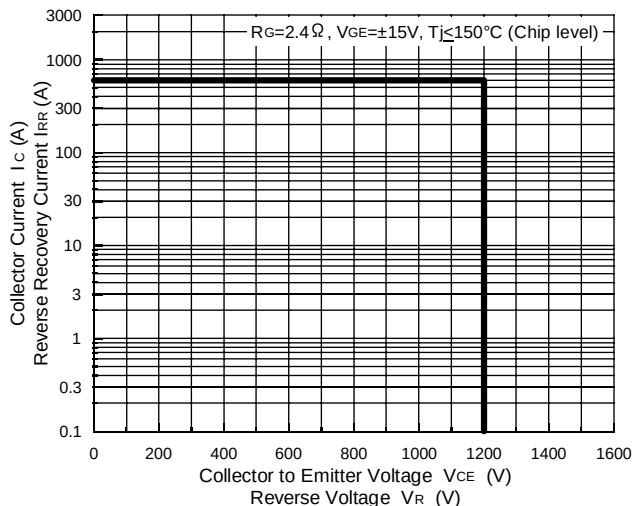


Fig.12- Transient Thermal Impedance

